

L Number	Hits	Search Text	DB	Time stamp
1	668	semiconductor and substrate and (trench or groove) and (thermal adj oxide) and ((silicon or polysilicon or Si) near4 fill\$) and (vapor adj deposition)	USPAT	2003/12/11 13:57
2	224	semiconductor and substrate and (trench or groove) and (thermal adj oxide) and ((silicon or polysilicon or Si) near4 fill\$) and (vapor adj deposition)	US-PGPUB	2003/12/11 13:57
3	0	semiconductor and substrate and (trench or groove) and (thermal adj oxide) and ((silicon or polysilicon or Si) near4 fill\$) and (vapor adj deposition)	EPO	2003/12/11 13:58
4	0	semiconductor and substrate and (trench or groove) and (thermal adj oxide) and ((silicon or polysilicon or Si) near4 fill\$) and (vapor adj deposition)	JPO	2003/12/11 13:58
5	5	semiconductor and substrate and (trench or groove) and (thermal adj oxide) and ((silicon or polysilicon or Si) near4 fill\$) and (vapor adj deposition)	DERWENT	2003/12/11 13:58
6	2	semiconductor and substrate and (trench or groove) and (thermal adj oxide) and ((silicon or polysilicon or Si) near4 fill\$) and (vapor adj deposition)	IBM_TDB	2003/12/11 13:59